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**Color Code:**

Red – Plasma Etching

Blue – Advanced Devices

For full patent text, please use patent number search feature at United States Patent and Trademark Office:

<http://patft.uspto.gov/netahtml/srchnum.htm>

US Patent Nr.	Title	Assignee	Filed	Date of Patent
6,613,673	Technique for elimination of pitting on silicon substrate during gate stack etch	Micron Technology, Inc.	8/29/01	9/2/03
6,613,689	Magnetically enhanced plasma oxide etch using hexafluorobutadiene	Applied Materials, Inc	5/13/02	9/2/03
6,617,202	Method for fabricating a full depletion type SOI device	Hynix Semiconductor Inc.	6/27/01	9/9/03
6,617,253	Plasma etching method using polymer deposition and method of forming contact hole using the plasma etching method	Samsung Electronics Co., Ltd.	7/20/00	9/9/03
6,617,257	Method of plasma etching organic antireflective coating	Lam Research Corporation	3/30/01	9/9/03
6,617,624	Metal gate electrode stack with a passivating metal nitride layer	Micron Technology, Inc.	3/15/01	9/9/03

6,620,335	Plasma etch reactor and method	Tegal Corporation	12/7/99	9/16/03
6,620,631	Plasma etch method for forming patterned layer with enhanced critical dimension (CD) control	Taiwan Semiconductor Manufacturing Co., Ltd	5/18/00	9/16/03
6,620,727	Aluminum hardmask for dielectric etch	Texas Instruments Incorporated	8/23/01	9/16/03
6,620,741	Method for controlling etch bias of carbon doped oxide films	Intel Corporation	6/10/02	9/16/03
6,621,114	MOS transistors with high-k dielectric gate insulator for reducing remote scattering	Advanced Micro Devices, Inc.	5/20/02	9/16/03
6,621,131	Semiconductor transistor having a stressed channel	Intel Corporation	11/1/01	9/16/03
6,623,653	System and method for etching adjoining layers of silicon and indium tin oxide	Sharp Laboratories of America, Inc.	6/12/01	9/23/03
6,624,032	Structure and process flow for fabrication of dual gate floating body integrated MOS transistors	Intel Corporation	3/20/02	9/23/03
6,624,068	Polysilicon processing using an anti-reflective dual layer hardmask for 193 nm lithography	Texas Instruments Incorporated	8/24/01	9/23/03
6,624,486	Method for low topography semiconductor device formation	International Business Machines Corporation	5/23/01	9/23/03

6,625,497	Semiconductor processing module with integrated feedback/feed forward metrology	Applied Materials Inc.	7/10/01	9/23/03
6,626,187	Method of reconditioning reaction chamber	Promos Technologies Inc.	3/23/01	9/30/03
6,627,360	Carbonization process for an etch mask	Advanced Micro Devices, Inc.	7/9/01	9/30/03
6,627,464	Adaptive plasma characterization system	ENI Technology, Inc.	2/7/01	9/30/03
6,627,510	Method of making self-aligned shallow trench isolation	Sharp Laboratories of America, Inc.	3/29/02	9/30/03
6,627,530	Patterning three dimensional structures	Matrix Semiconductor, Inc.	12/22/00	9/30/03
6,627,933	Method of forming minimally spaced word lines	Micron Technology, Inc.	10/23/02	9/30/03
6,627,972	Vertical bipolar transistor	Institut fuer Halbleiterphysik Frankfurt (Oder)	9/8/99	9/30/03